Ing. Ján Kuzmík, DrSc. is a senior researcher at the IEE and a Head of the department of III-V semiconductors. He received his PhD degree from Slovak Academy of Sciences in 1991. From 1991-1994 he was a research fellow at IESL FORTH Crete, Greece, involved in the ESPRIT project on technology of III-V microwave circuits and Brite Euram project on SiC devices. He was a JSPS fellow at the Kyoto Institute of Technology, Japan (SiC technology) in the period of 1996-1998. Since 2002 till 2011 he had been with the Institute for Solid State Electronics at the Technical University Vienna where he worked in the fields of electro-optical characterization and thermal effects in GaN HEMTs, III-V device physics, processing and characterization. In 2012 he was an invited professor at the University of Hokkaido, Japan. Dr. Kuzmik initiated the European project ULTRAGAN where he had been acting as a WP leader on the topic of device passivation and gate insulation. In EU project MORGAN he served as a scientific leader at TU Vienna and as a WP leader on the topic of device characterisation and modelling. Dr. Kuzmik is an author and co-author of more than 140 journal papers with more than 1900 citations; he had several invited talks in EU and Japan. He pioneered the fields of InAIN/GaN power electronics and GaN HEMTs thermal characterization techniques. He chaired the round table on future electron devices at ICNS 2009, Jeju, Korea, was a member of the program committee of IWN 2010 Florida, ISCS 2013 Kobe, IWN 2014 Wroclaw, ESREF 2014 Berlin, etc., and served as an expert for EU programmes.